

**Vishay Siliconix** 

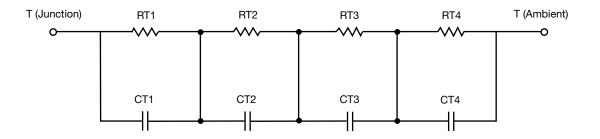
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



<b>R-C VALUES FOR TANK</b>	CONFIGURATION		
	THERMAL RES	SISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	n/a	83.8450m	n/a
RT2	n/a	391.1115m	n/a
RT3	n/a	414.1953u	n/a
RT4	n/a	125.7440m	n/a
·	THERMAL CAPAC	ITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	n/a	6.1312m	n/a
CT2	n/a	141.0248m	n/a
CT3	n/a	128.8503m	n/a
CT4	n/a	14.5497m	n/a

Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

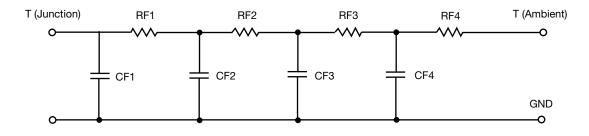
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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	n/a	55.8132m	n/a			
RF2	n/a	159.8584m	n/a			
RF3	n/a	303.4967m	n/a			
RF4	n/a	81.9897m	n/a			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	n/a	3.4586m	n/a			
CF2	n/a	2.4742m	n/a			
CF3	n/a	131.6245m	n/a			
CF4	n/a	2.7758m	n/a			

Note

• n/a indicates not applicable



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